

| specificazioni                          |                                                                                      |
|-----------------------------------------|--------------------------------------------------------------------------------------|
| Modello di prodotti                     | IRFB59N10DPBF                                                                        |
| fabbricante                             | International Rectifier (Infineon Technologies)                                      |
| Descrizione                             | MOSFET N-CH 100V 59A TO-220AB                                                        |
| Categoria                               | <a href="#">Prodotti a semiconduttore discreti</a> > <a href="#">Transistor-FET,</a> |
| Stato parte                             | 3606 pcs Stock                                                                       |
| Vgs (th) (max) a Id                     | 5.5V @ 250μA                                                                         |
| Tecnologia                              | MOSFET (Metal Oxide)                                                                 |
| Contenitore dispositivo fornitore       | TO-220AB                                                                             |
| Serie                                   | HEXFET®                                                                              |
| Rds On (max) a Id, Vgs                  | 25 mOhm @ 35.4A, 10V                                                                 |
| Dissipazione di potenza (max)           | 3.8W (Ta), 200W (Tc)                                                                 |
| imballaggio                             | Tube                                                                                 |
| Contenitore / involucro                 | TO-220-3                                                                             |
| temperatura di esercizio                | -55°C ~ 175°C (TJ)                                                                   |
| Tipo montaggio                          | Through Hole                                                                         |
| Capacità di ingresso (Ciss) (Max) @ Vds | 2450pF @ 25V                                                                         |
| Carica Gate (Qg) (Max) @ Vgs            | 114nC @ 10V                                                                          |
| Tipo FET                                | N-Channel                                                                            |
| Caratteristica FET                      | -                                                                                    |
| Tensione drain-source (Vdss)            | 100V                                                                                 |
| Corrente - Drain continuo (Id) @ 25 ° C | 59A (Tc)                                                                             |

|                                                                                                                                                                           |                                                                                                                                          |                                                                                                                                                   |                                                                                                                                                                               |
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|  <p><b>IRFB5N50L</b><br/>IR<br/>IRFB5N50L IR</p>                                       |  <p><b>IRFB61N15D</b><br/>IR<br/>IRFB61N15D IR</p>    |  <p><b>IRFB60N10</b><br/>IR<br/>IR TO-220</p>                 |  <p><b>IRFB61N15DPBF</b><br/>Infineon Technologies<br/>MOSFET N-CH 150V 60A TO-220AB</p> |
|  <p><b>IRFB5620PBF</b><br/>Infineon Technologies<br/>MOSFET N-CH 200V 25A TO-220AB</p> |  <p><b>IRFB61N15DPBF MOS</b><br/>IR<br/>IR TO-220</p> |  <p><b>IRFB5620PBF MOS</b><br/>VBSEMI<br/>VBSEMI TO-220AB</p> |  <p><b>IRFB59N10D</b><br/>IR<br/>IRFB59N10D IR</p>                                       |

Di Più

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